



FPN660 FPN660A



TO-226

PNP Low Saturation Transistor

These devices are designed for high current gain and low saturation voltage with collector currents up to 3.0 A continuous. Sourced from Process PA.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	60	V
V_{CBO}	Collector-Base Voltage	80	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current - Continuous	3.0	A
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
- 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		FPN660 / FPN660A	
P_D	Total Device Dissipation	1.0	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	50	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125	°C/W

PNP Low Saturation Transistor

(continued)

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHARACTERISTICS					
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 10 mA, I _B = 0	60		V
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = 100 µA, I _E = 0	80		V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = 100 µA, I _C = 0	5.0		V
I _{CBO}	Collector Cutoff Current	V _{CB} = 30 V, I _E = 0 V _{CB} = 30 V, I _E = 0, TA = 100°C	100 10		nA µA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 4.0 V, I _C = 0	100		nA
ON CHARACTERISTICS*					
h _{FE}	DC Current Gain	I _C = 100 mA, V _{CE} = 2.0 V I _C = 500 mA, V _{CE} = 2.0 V	660 660A	70 100 250 80 40	300 550
		I _C = 1.0 A, V _{CE} = 2.0 V I _C = 2.0 A, V _{CE} = 2.0 V			
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 1.0 A, I _B = 100 mA I _C = 2.0 A, I _B = 200 mA	660 660A	300 450 400	mV mV mV
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 1.0 A, I _B = 100 mA		1.25	V
V _{BE(on)}	Base-Emitter Saturation Voltage	I _C = 1.0 A, V _{CE} = 2.0 V		1.0	V
SMALL SIGNAL CHARACTERISTICS					
C _{obo}	Output Capacitance	V _{CB} = 10 V, I _E = 0, f = 1.0 MHz		45	pF
F _T	Transition Frequency	I _C = 100 mA, V _{CE} = 5.0 V, f = 100 MHz	75		MHz

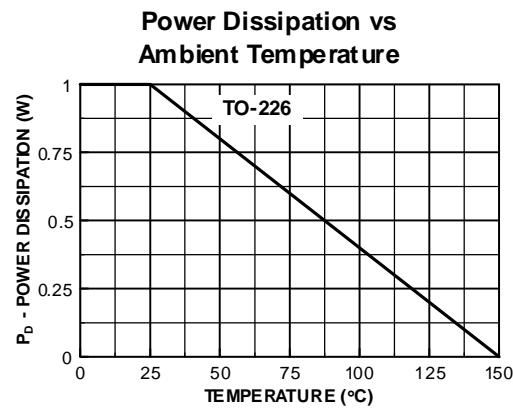
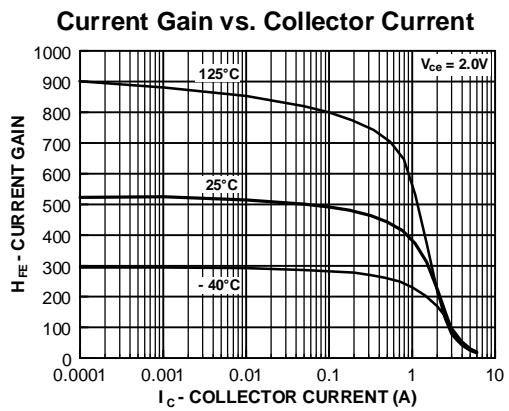
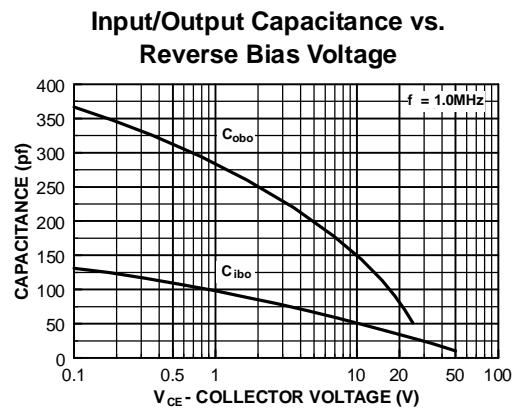
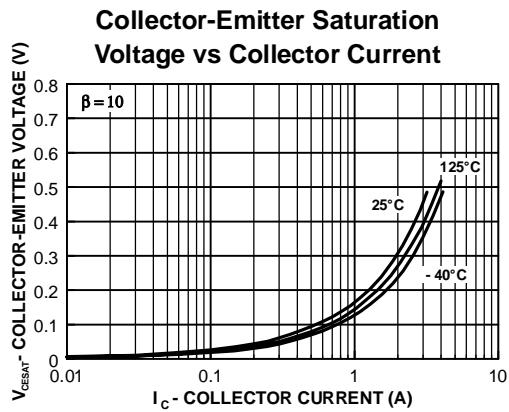
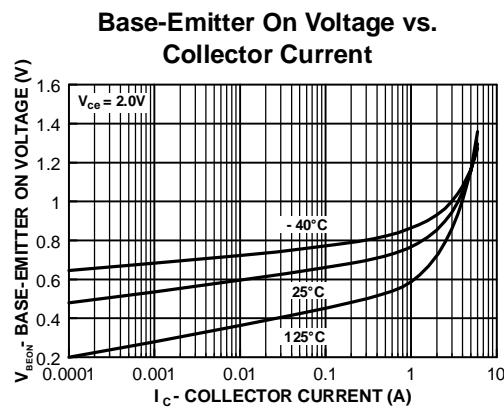
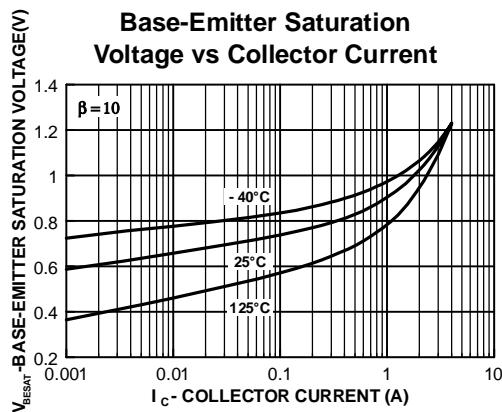
*Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%

NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.

PNP Low Saturation Transistor

(continued)

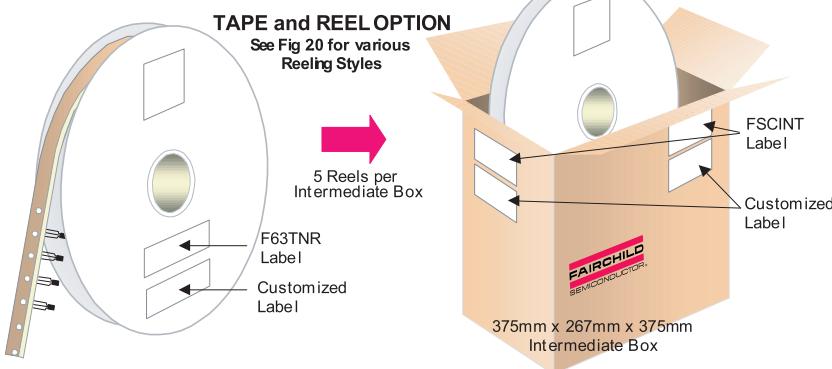
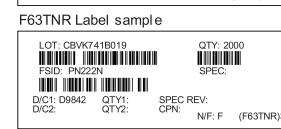
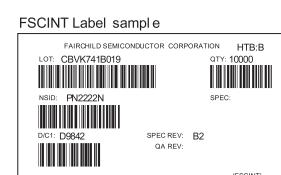
Typical Characteristics



TO-226AE Tape and Reel Data



TO-226AE Packaging
Configuration: Figure 1.0



TO-226AE TNR/AMMO PACKING INFORMATION

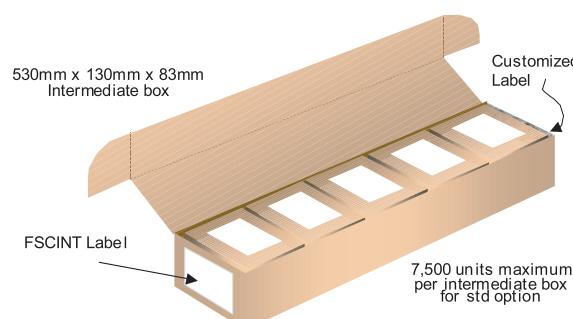
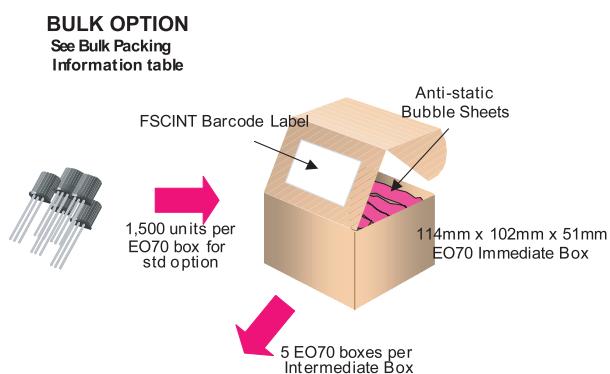
Packing	Style	Quantity	EOL code
Reel	A	2,000	D26Z
	E	2,000	D27Z
Ammo	M	2,000	D74Z
	P	2,000	D75Z

Unit weight = 0.300gm
Reel weight with components = 0.868 kg
Ammo weight with components = 0.880 kg
Max quantity per intermediate box = 10,000 units



(TO-226AE) BULK PACKING INFORMATION

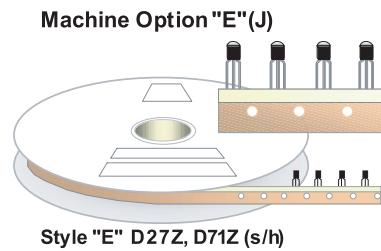
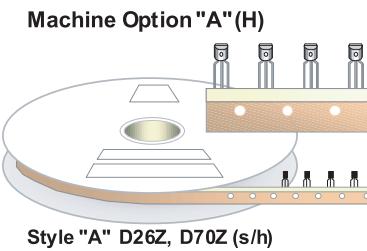
EOL CODE	DESCRIPTION	LEADCLIP DIMENSION	QUANTITY
J18Z	TO-18 OPTION STD	NO LEAD CLIP	1.0 K / BOX
J05Z	TO-5 OPTION STD	NO LEAD CLIP	1.0 K / BOX
NO EOL CODE	TO-226 STANDARD STRAIGHT	NO LEADCLIP	1.5 K / BOX



TO-226AE Tape and Reel Data, continued

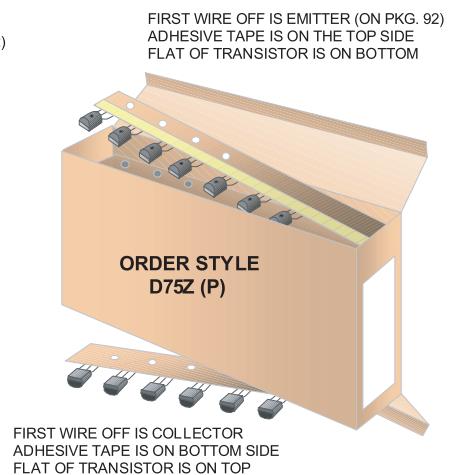
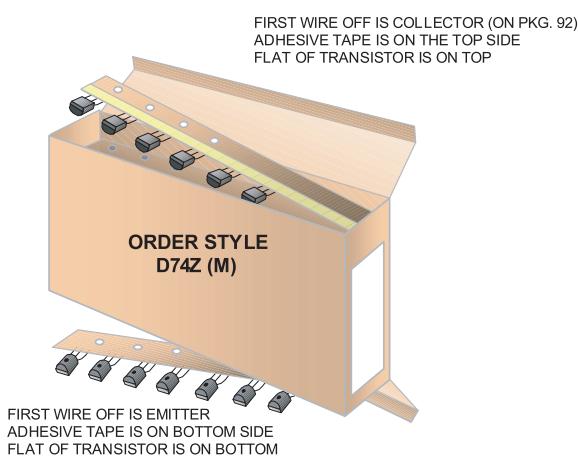
TO-226AE Reeling Style

Configuration: Figure 2.0



TO-226AE Radial Ammo Packaging

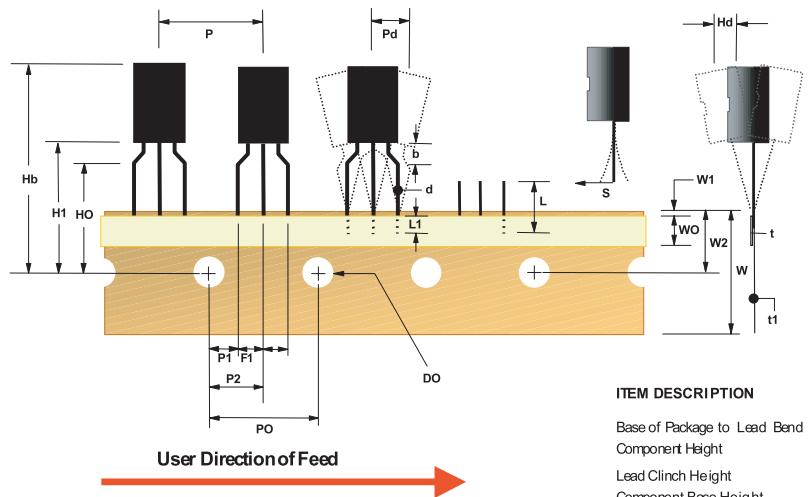
Configuration: Figure 3.0



TO-226AE Tape and Reel Data, continued

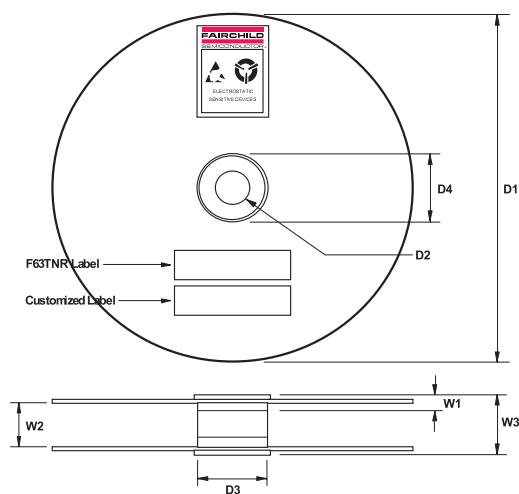
TO-226AE Tape and Reel Taping

Dimension Configuration: Figure 4.0



TO-226AE Reel

Configuration: Figure 5.0



ITEM DESCRIPTION	SYMBOL	DIMENSION
Base of Package to Lead Bend	b	0.098 (max)
Component Height	Hb	1.078 (+0.0050)
Lead Clinch Height	HO	0.630 (+0.020)
Component Base Height	H1	0.748 (+0.0020)
Component Alignment (side/side)	Pd	0.040 (max)
Component Alignment (front/back)	Hd	0.031 (max)
Component Pitch	P	0.500 (+0.0020)
Feed Hole Pitch	PO	0.500 (+0.008)
Hole Center to First Lead	P1	0.150 (+0.009, -0.010)
Hole Center to Component Center	P2	0.247 (+0.007)
Lead Spread	F1/F2	0.104 (+0.010)
Lead Thickness	d	0.018 (+0.002, -0.003)
Cut Lead Length	L	0.429 (max)
Taped Lead Length	L1	0.209 (+0.051, -0.052)
Taped Lead Thickness	t	0.032 (+0.006)
Carrier Tape Thickness	t1	0.021 (+0.006)
Carrier Tape Width	W	0.708 (+0.020, -0.019)
Hold - down Tape Width	WO	0.236 (+0.012)
Hold - down Tape position	W1	0.035 (max)
Feed Hole Position	W2	0.360 (+0.025)
Sprocket Hole Diameter	DO	0.157 (+0.008, -0.007)
Lead Spring Out	S	0.004 (max)

Note: All dimensions are in inches.

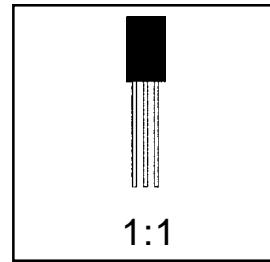
ITEM DESCRIPTION	SYMBOL	MINIMUM	MAXIMUM
Reel Diameter	D1	13975	14025
Arbor Hole Diameter (Standard)	D2	1.160	1.200
(Small Hole)	D2	0.650	0.700
Core Diameter	D3	3.100	3.300
Hub Recess Inner Diameter	D4	2.700	3.100
Hub Recess Depth	W1	0.370	0.570
Range to Range Inner Width	W2	1.630	1.690
Hub to Hub Center Width	W3		2.090

Note: All dimensions are in inches

TO-226AE Package Dimensions

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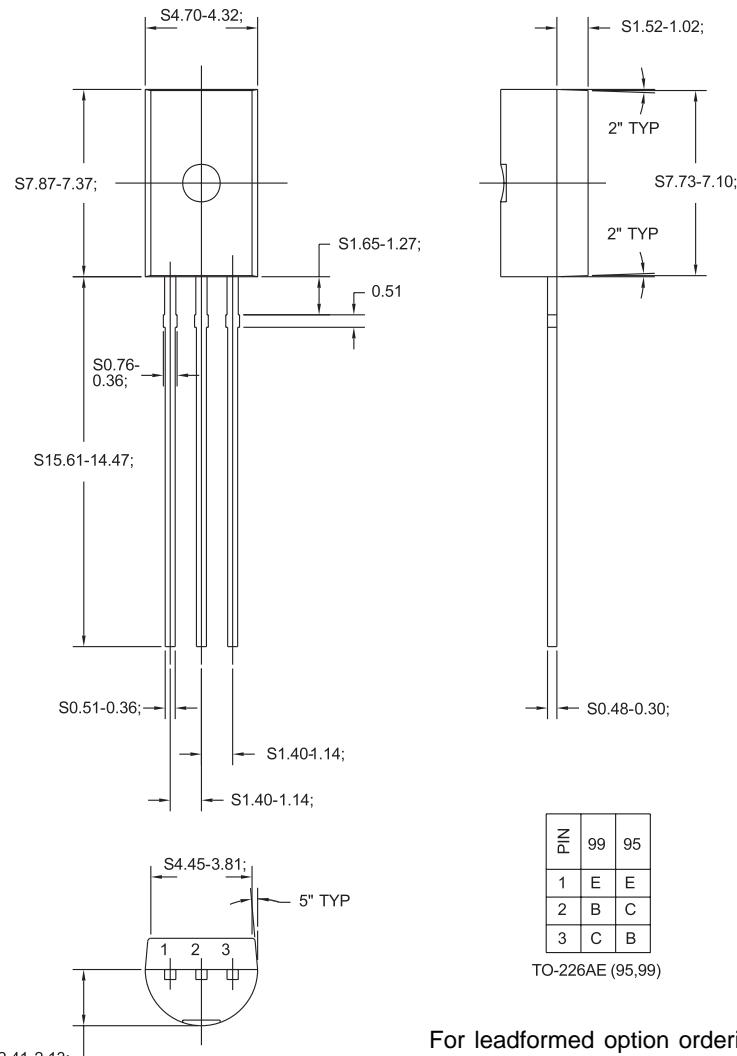
TO-226AE (FS PKG Code 95, 99)



Scale 1:1 on letter size paper

Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.300



For leadformed option ordering,
refer to Tape & Reel data information.

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